

100V 0.3A Fast Switching Diode - 1N914

Small-Signal high speed switching diode in bare die form

Rev 1.1 24/10/24

Features:

- Fast Switching Speed
- High conductance
- General purpose switching applications
- High reliability tested grades.

Ordering Information

The following part suffixes apply:

- No suffix MIL-STD-750 /2073 Visual Inspection
- "H" MIL-STD-750 /2073 Visual Inspection+ MIL-PRF-38534 Class H LAT
- "K" MIL-STD-750 /2073 Visual Inspection+ MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

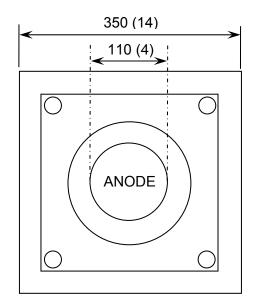
For further information on LAT process flows see below.

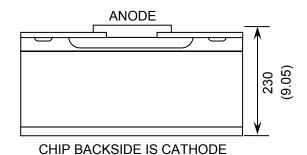
www.siliconsupplies.com\quality\bare-die-lot-qualification

Supply Formats:

- Default Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape By specific request
- Unsawn Wafer By specific request
- Die Thickness <> 230µm(9 Mils) On request
- With additional electrical selection On request

Die Dimensions in µm (mils)





Mechanical Specification

Die Size (Unsawn)	350 x 350 13.78 x 13.78	µm mils
Anode Pad Size	110 Ø 4.3 Ø	µm mils
Die Thickness	230 (±15) 9.05 (±0.59)	µm mils
Top Metal Composition	Al	
Back Metal Composition	AuAs	





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Absolute Maximum Ratings¹ T_J = 25°C unless otherwise stated

PARAMETER	SYMBOL	VALUE		UNIT		
Non-repetitive Peak Reverse Voltage	V_{RSM}	105	105		105 V	
Repetitive Peak Reverse Voltage	V_{RRM}	100		V		
Average Rectified Forward Current	Io	200		mA		
DC Forward Current	I _F	300		mA		
Recurrent Peak Forward Current	lf	400		mA		
Non-repetitive	leau	Pulse width 1s	1	A		
Peak forward surge current	IFSM	Pulse width 1µs	4			
Power Dissipation	P_D	200		200 mW		mW
Operating Junction temperature	TJ	-55 to 175		°C		
Storage Temperature Range	T _{STG}	-65 to 200		°C		

^{1.} Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability.

Electrical Characteristics T_J = 25°C unless otherwise stated

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Breakdown Voltage	V _R	I _R = 100μA	100	-	-	V
	VR [$I_R = 5\mu A$	75	-	-	V
Forward Voltage ²		I _F = 5mA	-	-	0.72	V
	V _F	I _F = 20mA	-	-	1	
		I _F = 100mA	-	-	1	
Reverse Leakage		V _R = 20V	-	-	0.025	μА
	I _R	$V_R = 20V, T_J = 150^{\circ}C$	-	-	50	
	ik [V _R = 75V	-	-	5	
		V _R = 100V	-	-	10	
Total Capacitance	C _T	$V_R = 0V$, $f = 1MHz$	-	-	4	pF
Reverse Recovery Time	t _{rr}	$I_F = 10mA, V_R = 6V (600mA)$ $I_{rr} = 1mA, R_L = 100\Omega$	-	-	4	ns

2. Pulse Width = 8.3ms, Non-recurrent square wave





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Typical Characteristics T_J = 25°C unless otherwise stated

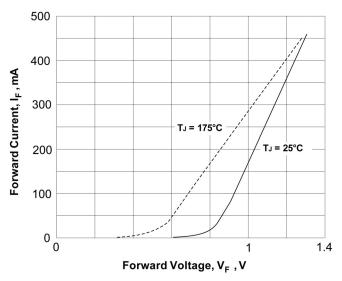


FIGURE 1. Forward Voltage Characteristics

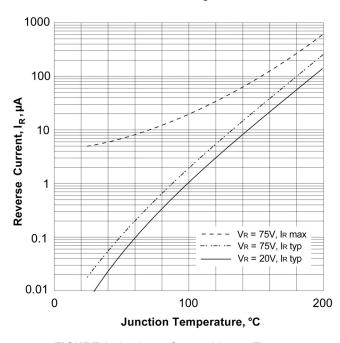


FIGURE 2. Leakage Current Versus Temperature

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